

N-channel 40 V, 2.5 mΩ standard level MOSFET in LFPAK56 14 September 2017 Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - · Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching



4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	190	W
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.5	5 2.13	2.5	mΩ
Dynamic ch	aracteristics					-
Q _{GD}	gate-drain charge	$\begin{split} I_D &= 25 \text{ A}; \text{ V}_{DS} = 32 \text{ V}; \text{ V}_{GS} = 10 \text{ V}; \\ T_j &= 25 \text{ °C}; \text{ Fig. 12}; \text{ Fig. 13} \end{split}$	-	8.9	22	nC
Source-drai	n diode					
Q _r	recovered charge	$ I_S = 25 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_j = 25 \text{ °C} $	-	22.7	-	nC
S	softness factor	$ I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16} $	-	0.79	-	

5. Pinning information

Table 2. F	Table 2. Pinning information						
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source	mb	D			
2	S	source	ل ا دے ا				
3	S	source		G L F A			
4	G	gate		mbb076 S			
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)				

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK7Y2R5-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals; 4.9 mm x 4.45 mm x 1 mm body	SOT669		

7. Marking

٦	Table 4. Marking codes	
	Type number	Marking code
	BUK7Y2R5-40H	72H540

8. Limiting values

Table 5. Limiting values

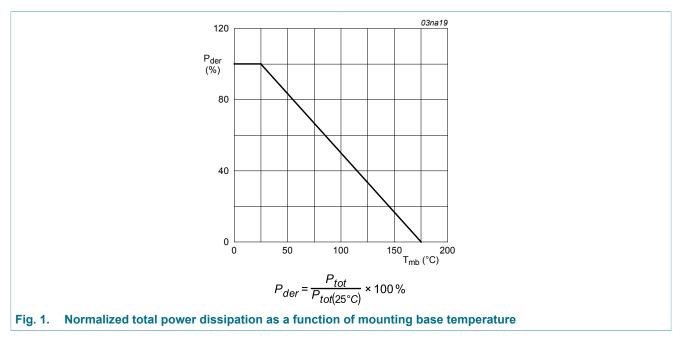
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	190	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C		-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 2		-	600	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode		·			
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 120 \text{ A}; \ V_{sup} \leq \ 40 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 3 \end{array}$	[2] [3]	-	82.1	mJ

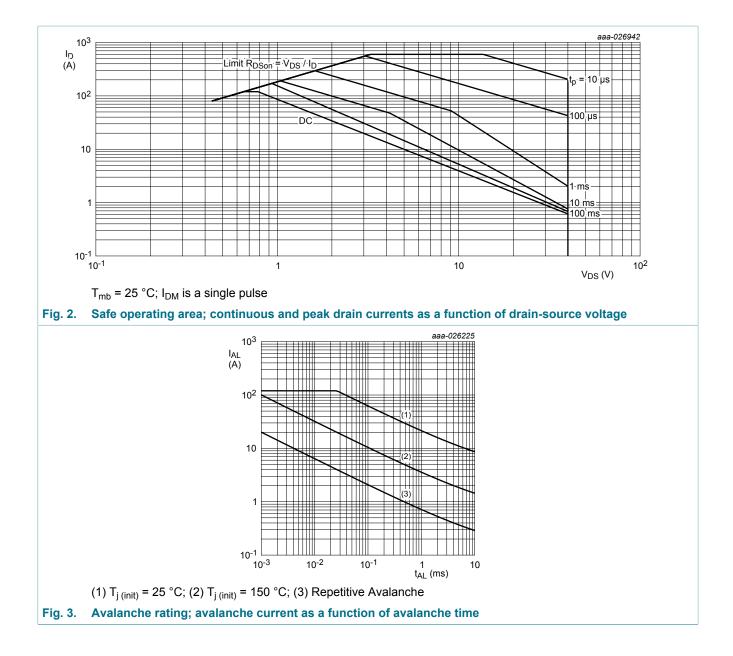
[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

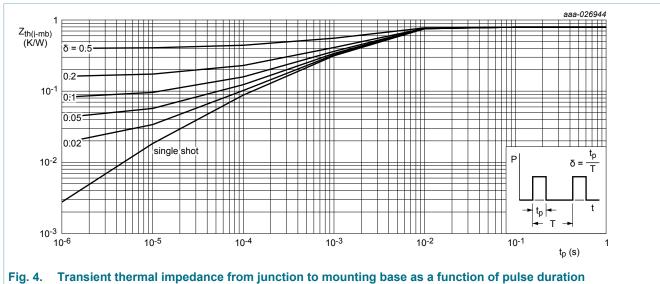


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9. Thermal characteristics

Table 6. Therm	nal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.63	0.79	K/W



BUK7Y2R5-40H

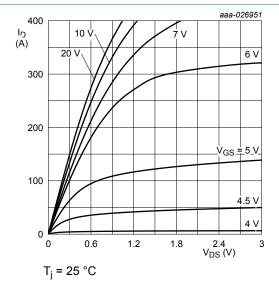
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	· · · · ·				
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.7	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 8</u> ; Fig. 9	2.4	3	3.6	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 8</u>	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 8</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	1.2	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	113	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.5	2.13	2.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 11	2.12	2.82	3.98	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.34	3.18	4.38	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	2.94	4.07	5.45	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.3	0.74	1.85	Ω
Dynamic ch	aracteristics	· · ·				_
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V;	-	45.8	79	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 12; Fig. 13</u>	-	12.7	19	nC
Q _{GD}	gate-drain charge		-	8.9	22	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	3193	4790	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	831	1163	pF
C _{rss}	reverse transfer capacitance		-	150	330	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	12.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	10.3	-	ns
t _{d(off)}	turn-off delay time	1	-	27.5	-	ns
t _f	fall time		-	13	-	ns
Source-drai	n diode				1	
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	29.3	-	ns
Qr	recovered charge			-	22.7	-	nC
S softness factor	softness factor	$ I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16} $		-	0.79	-	
		$ I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16} $		-	0.65	-	



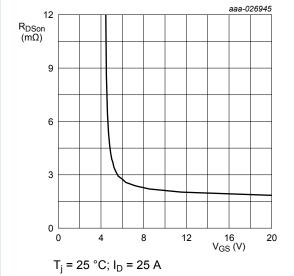


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

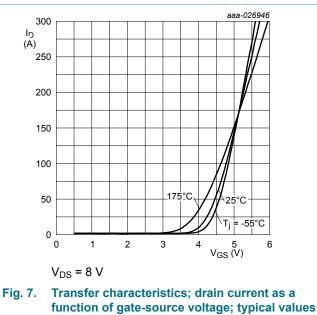
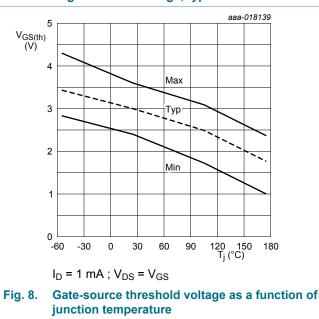
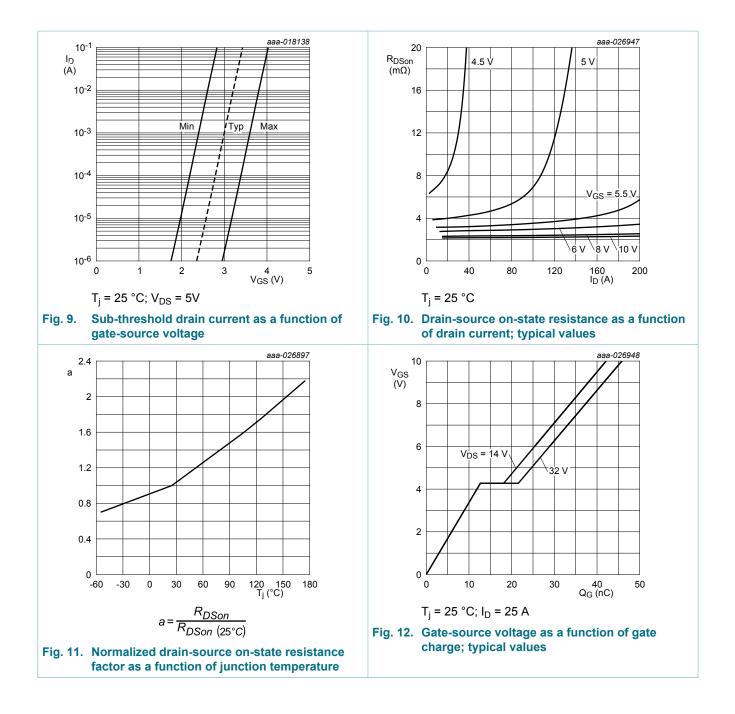


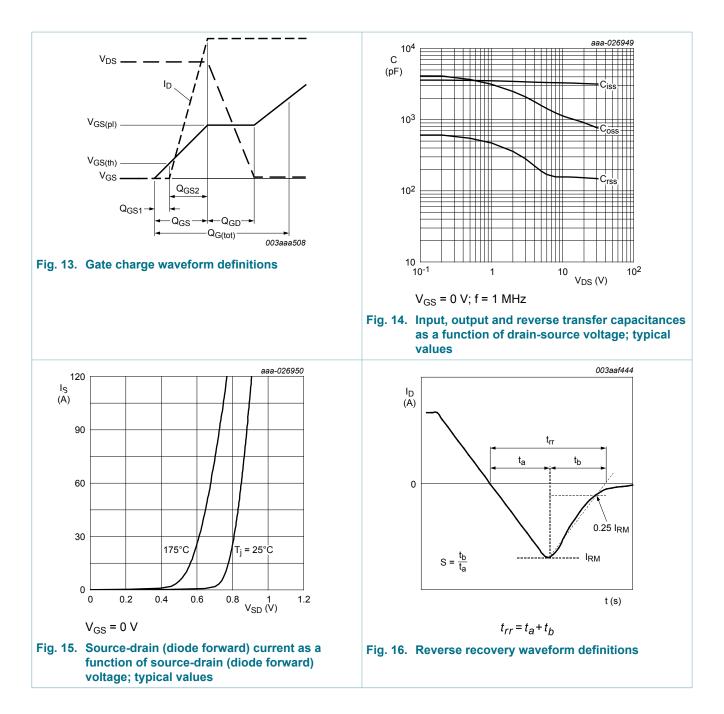
Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



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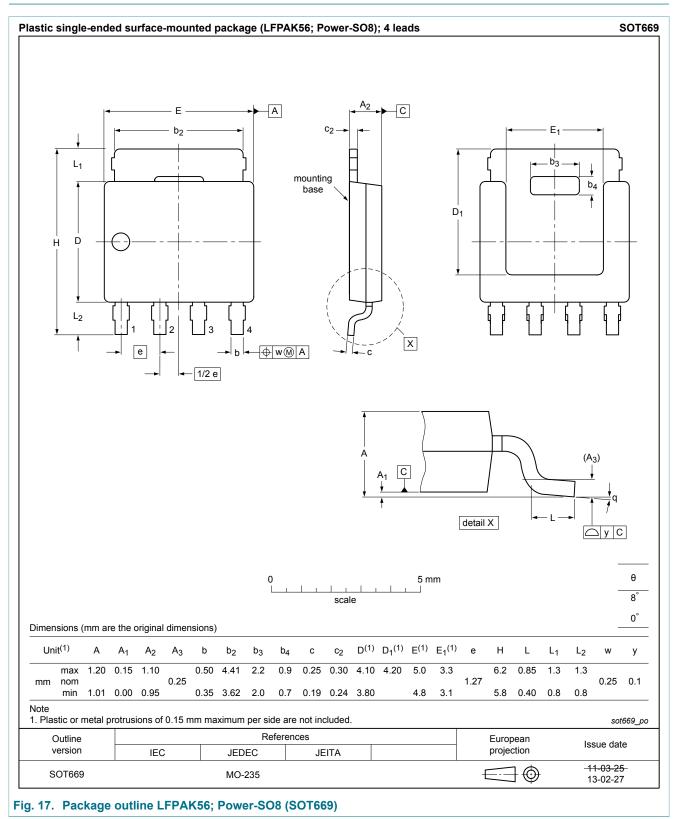


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11. Package outline



BUK7Y2R5-40H

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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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